

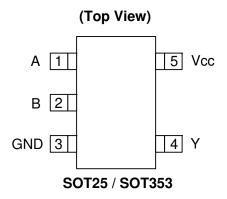
SINGLE 2 INPUT POSITIVE NAND GATE

Description

The 74AHCT1G00 is a single 2-input positive NAND gate with a standard totem pole output. The device is designed for operation with a power supply range of 4.5V to 5.5V. The gate performs the positive Boolean function:

 $Y = \overline{A \bullet B} \text{ or } Y = \overline{A} + \overline{B}$

Pin Assignments



Features

- Supply Voltage Range from 4.5V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
 - o Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- SOT25 and SOT353: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

Applications

- General Purpose Logic
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

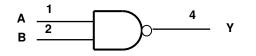


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Pin Descriptions

Pin Name	Pin No.	Description
А	1	Data Input
В	2	Data Input
GND	3	Ground
Y	4	Data Output
V _{CC}	5	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
Α	В	Y
Н	Н	L
L	Х	Н
Х	L	н



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Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-20	mA
I _{OK}	Output Clamp Current ($V_O < 0$ or $V_O > V_{CC}$)	±20	mA
Ι _Ο	Continuous output current (V _O = 0 to V _{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	Continuous current through GND	-50	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		4.5	5.5	V
V _{IH}	High-level Input Voltage		2.0		V
VIL	Low-level input voltage			0.8	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
I _{ОН}	High-level output current			-8	mA
I _{OL}	Low-level output current			8	mA
Δt/ΔV	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at V_{CC} or Ground.



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Electrical Characteristics

		T			25ºC		-40ºC 1	to 85ºC	-40ºC to	o 125ºC	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Min	Max	Min	Max	Unit
	High Level	I _{OH} = -50μA	4.5V	4.4	4.5		4.4		4.4		
V _{OH}	Output Voltage	I _{OH} = -8mA	4.5V	3.94			3.8		3.70		V
V	Low Level	I _{OL} = 50μA	4.5V		0	0.1		0.1		0.1	V
V _{OL}	Output Voltage	$I_{OL} = 8mA$	4.5V			0.36		0.44		0.55	v
l _l	Input Current	$V_{I} = 5.5V \text{ or } GND$	0 to 5.5V			± 0.1		± 1		±2	μA
I _{CC}	Supply Current	V _I = 5.5V or GND I _O =0	5.5V			1		10		40	μA
Ci	Input Capacitance	V _I = V _{CC} – or GND	5.5V		2.0	10		10		10	pF
ΔI _{CC}	Additional Supply Current	One input at 3.4V Other inputs at V _{CC} or GND	5.5V			1.35		1.5			mA
_	Thermal Resistance	SOT25			204						°0.00
θ_{JA}	Junction-to- Ambient	SOT353	(Note 4)		371						°C/W
0	Thermal Resistance	SOT25	(NI=+=_4)		52						°0.00
θ _{JC}	Junction-to- Case	SOT353	(Note 4)		143						°C/W

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

 $V_{CC} = 5V \pm 0.5V$ (see Figure 1)

	aramatar	From	то			25ºC		-40ºC t	o 85ºC	-40ºC to	o 125ºC	Unit
F	arameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	+	A or B	V	$C_L=15pF$	0.6	3.6	6.2	0.6	7.1	0.6	8.0	ns
	٩	AOID	ř	$C_L=50pF$	0.6	5.0	7.9	0.6	9.0	0.6	10.0	ns

Operating Characteristics

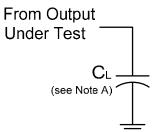
 $T_A = 25 \ ^{o}C$

	Parameter	Test Conditions	V _{CC} = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 1 MHz No Load	11	pF

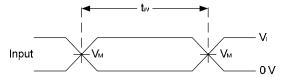


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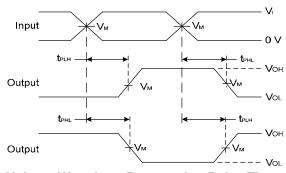
Parameter Measurement Information



Vcc	In	puts	V	0
VCC	VI	t _r /t _f	V _M	υL
5V±0.5V	3 V	≤3ns	1.5V	15pF
5V±0.5V	3 V	≤3ns	1.5V	50pF



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate ≤ 1 MHz.

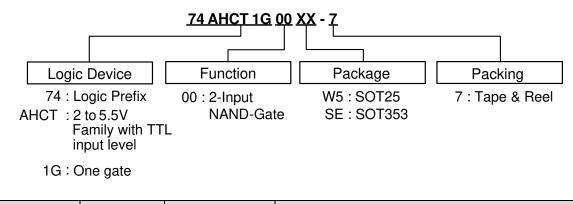
- C. Inputs are measured separately one transition per measurement.
- D. tPLH and tPHL are the same as tpd.

74AHCT1G00 Document number: DS35179 Rev. 1-2



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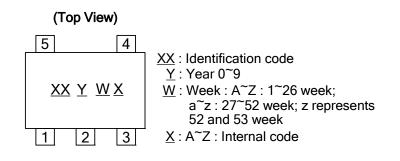
Ordering Information



Davias	Package	Packaging	7" Tape and Reel		
Device	Code	(Note 5)	Quantity	Part Number Suffix	
74AHCT1G00W5-7	W5	SOT25	3000/Tape & Reel	-7	
74AHCT1G00SE-7	SE	SOT353	3000/Tape & Reel	-7	
		Device Code 74AHCT1G00W5-7 W5	DeviceCode(Note 5)74AHCT1G00W5-7W5SOT25	Device Code (Note 5) Quantity 74AHCT1G00W5-7 W5 SOT25 3000/Tape & Reel	

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



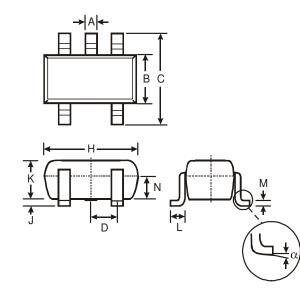
Part Number	Package	Identification Code
74AHCT1G00W5	SOT25	ZR
74AHCT1G00SE	SOT353	ZR



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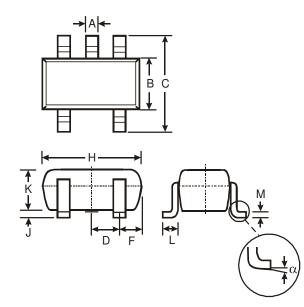
Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



	SOT	25	
Dim	Min	Max	Тур
Α	0.35	0.50	0.38
В	1.50	1.70	1.60
С	2.70	3.00	2.80
D	_		0.95
н	2.90	3.10	3.00
J	0.013	0.10	0.05
К	1.00	1.30	1.10
L	0.35	0.55	0.40
М	0.10	0.20	0.15
Ν	0.70	0.80	0.75
α	0°	8°	_
All D	imensi	ons in	mm

(2) Package Type: SOT353



	SOT353						
Dim	Min	Max					
Α	0.10	0.30					
в	1.15	1.35					
С	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
Н	1.80	2.20					
J	0	0.10					
К	0.90	1.00					
L	0.25	0.40					
М	0.10	0.22					
α	0°	8°					
All Di	mensions	in mm					



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